

Low VCEsat (BISS) transistors

Manufacturers	NXP Semiconductor
Package/Case	SOT89
Product Type	Discrete Semiconductors
RoHS	
Lifecycle	



Images are for reference only

Please submit RFQ for PBSS4250X or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

PBSS4250X is a type of PNP bipolar junction transistor (BJT) that is designed for high-speed switching applications. It is manufactured by NXP Semiconductors and features a low collector-emitter saturation voltage and a high collector current.

Features

- Collector-emitter voltage (VCEO): -50V
- Collector current (IC): -2A
- Emitter-base voltage (VEBO): -5V
- Collector-emitter saturation voltage (VCEsat): 250mV @ -1.5A
- Transition frequency (fT): 150MHz

Application

- BC856B
- BC856C
- BC857B
- BC857C
- BC858B
- BC858C
- BC859B
- BC859C



Related Products



[PBSS304NX](#)

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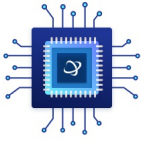
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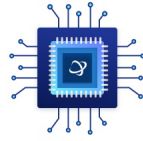
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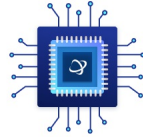
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